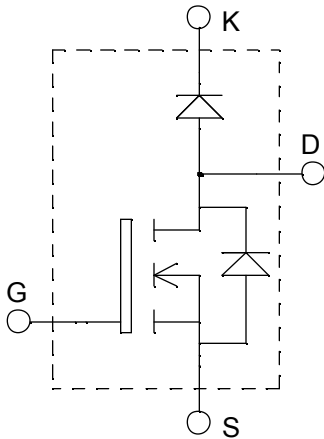


**ISOTOP® Boost chopper  
MOSFET Power Module**

$V_{DSS} = 200V$   
 $R_{DSon} = 22m\Omega \text{ max @ } T_j = 25^\circ C$   
 $I_D = 97A \text{ @ } T_c = 25^\circ C$



**Application**

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction
- Brake switch

**Features**

- Power MOS V<sup>®</sup> MOSFETs
  - Low  $R_{DSon}$
  - Low input and Miller capacitance
  - Low gate charge
  - Fast intrinsic diode
  - Avalanche energy rated
  - Very rugged
- ISOTOP® Package (SOT-227)
- Very low stray inductance
- High level of integration

**Benefits**

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Very rugged
- Low profile

**Absolute maximum ratings**

Symbol	Parameter	Max ratings	Unit
$V_{DSS}$	Drain - Source Breakdown Voltage	200	V
$I_D$	Continuous Drain Current	$T_c = 25^\circ C$	97
		$T_c = 80^\circ C$	72
$I_{DM}$	Pulsed Drain current	388	A
$V_{GS}$	Gate - Source Voltage	$\pm 30$	V
$R_{DSon}$	Drain - Source ON Resistance	22	$m\Omega$
$P_D$	Maximum Power Dissipation	$T_c = 25^\circ C$	450
$I_{AR}$	Avalanche current (repetitive and non repetitive)	97	A
$E_{AR}$	Repetitive Avalanche Energy	50	mJ
$E_{AS}$	Single Pulse Avalanche Energy	2500	
$I_{FAV}$	Maximum Average Forward Current	Duty cycle=0.5	A
$I_{FRMS}$	RMS Forward Current (Square wave, 50% duty)	$T_c = 90^\circ C$	
			47

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

### Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$BV_{DSS}$	Drain - Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	200			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 200V, T_j = 25^\circ\text{C}$			25	$\mu A$
		$V_{GS} = 0V, V_{DS} = 160V, T_j = 125^\circ\text{C}$			250	
$R_{DS(on)}$	Drain - Source on Resistance	$V_{GS} = 10V, I_D = 48.5A$			22	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 2.5mA$	2		4	V
$I_{GSS}$	Gate - Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 100$	nA

### Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{iss}$	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1MHz$		8500		pF
$C_{oss}$	Output Capacitance			1950		
$C_{rss}$	Reverse Transfer Capacitance			560		
$Q_g$	Total gate Charge	$V_{GS} = 10V$ $V_{Bus} = 100V$ $I_D = 97A @ T_j = 25^\circ\text{C}$		290		nC
$Q_{gs}$	Gate - Source Charge			66		
$Q_{gd}$	Gate - Drain Charge			120		
$T_{d(on)}$	Turn-on Delay Time	$V_{GS} = 15V$ $V_{Bus} = 100V$ $I_D = 97A @ T_j = 25^\circ\text{C}$ $R_G = 0.6\Omega$		16		ns
$T_r$	Rise Time			25		
$T_{d(off)}$	Turn-off Delay Time			48		
$T_f$	Fall Time			8		

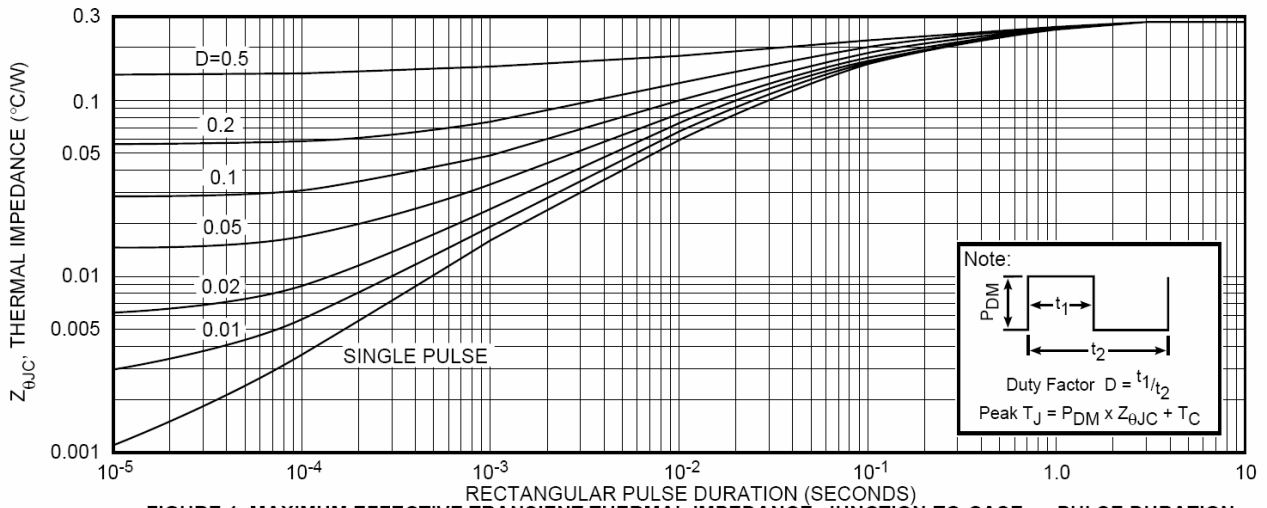
### Diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
$V_F$	Diode Forward Voltage	$I_F = 30A$		1.1	1.15	V	
		$I_F = 60A$		1.4			
		$I_F = 30A, T_j = 125^\circ\text{C}$		0.9			
$I_{RM}$	Maximum Reverse Leakage Current	$V_R = 200V, T_j = 25^\circ\text{C}$			250	$\mu A$	
		$V_R = 200V, T_j = 125^\circ\text{C}$			500		
$C_T$	Junction Capacitance	$V_R = 200V$		94		pF	
$t_{rr}$	Reverse Recovery Time	$I_F = 1A, V_R = 30V$ $di/dt = 200A/\mu s$	$T_j = 25^\circ\text{C}$		21	ns	
				$T_j = 25^\circ\text{C}$			24
				$T_j = 125^\circ\text{C}$			48
$I_{RRM}$	Maximum Reverse Recovery Current	$I_F = 30A$ $V_R = 133V$ $di/dt = 200A/\mu s$	$T_j = 25^\circ\text{C}$		3	A	
				$T_j = 125^\circ\text{C}$			6
				$T_j = 25^\circ\text{C}$			33
$Q_{rr}$	Reverse Recovery Charge	$I_F = 30A$ $V_R = 133V$ $di/dt = 1000A/\mu s$	$T_j = 125^\circ\text{C}$		150	nC	
				$T_j = 25^\circ\text{C}$			31
$t_{rr}$	Reverse Recovery Time	$I_F = 30A$ $V_R = 133V$ $di/dt = 1000A/\mu s$	$T_j = 125^\circ\text{C}$		31	ns	
$Q_{rr}$	Reverse Recovery Charge				335	nC	
$I_{RRM}$	Maximum Reverse Recovery Current					19	A

**Thermal and package characteristics**

Symbol	Characteristic	Min	Typ	Max	Unit
R <sub>thJC</sub>	Junction to Case	MOSFET		0.28	°C/W
		Diode		1.21	
R <sub>thJA</sub>	Junction to Ambient (IGBT & Diode)			20	
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t = 1 min, I <sub>isol</sub> < 1mA, 50/60Hz	2500			V
T <sub>J</sub> , T <sub>STG</sub>	Storage Temperature Range	-55		150	°C
T <sub>L</sub>	Max Lead Temp for Soldering: 0.063" from case for 10 sec			300	
Torque	Mounting torque (Mounting = 8-32 or 4mm Machine and terminals = 4mm Machine)			1.5	N.m
Wt	Package Weight		29.2		g

**Typical MOSFET Performance Curve**



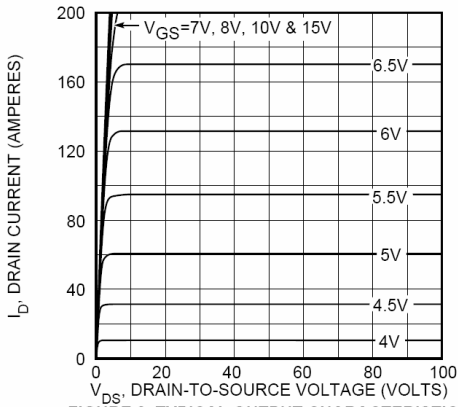


FIGURE 2, TYPICAL OUTPUT CHARACTERISTICS

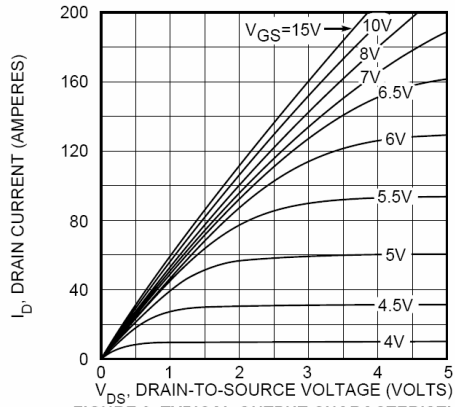


FIGURE 3, TYPICAL OUTPUT CHARACTERISTICS

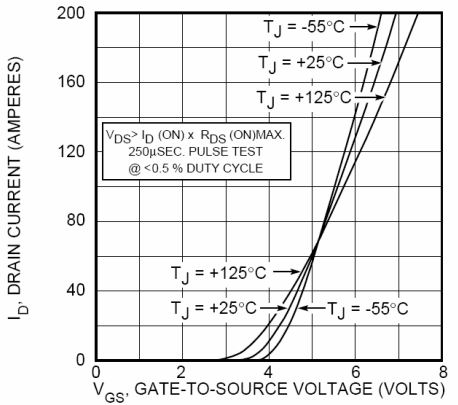


FIGURE 4, TYPICAL TRANSFER CHARACTERISTICS

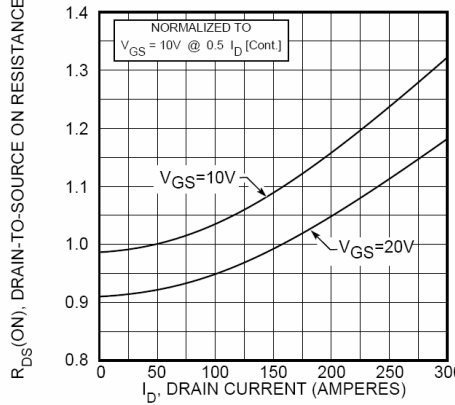


FIGURE 5,  $R_{DS(ON)}$  vs DRAIN CURRENT

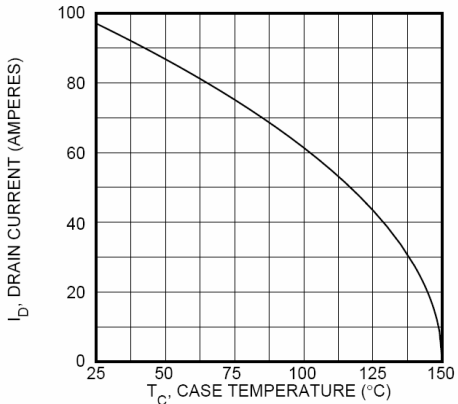


FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

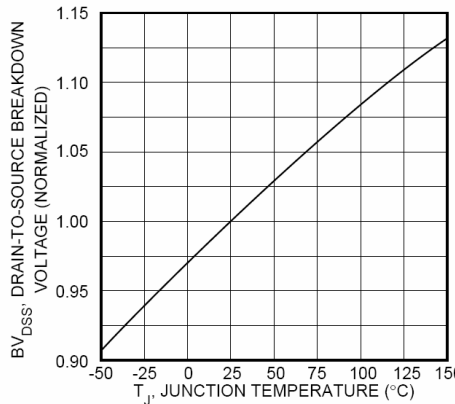


FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE

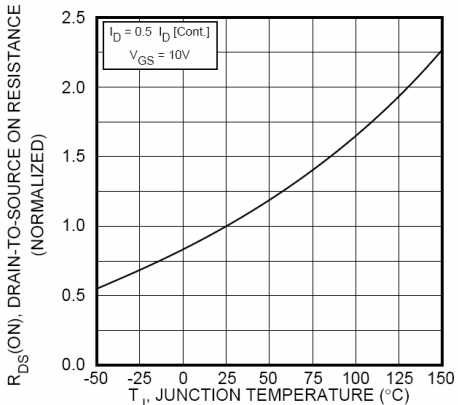


FIGURE 8, ON-RESISTANCE vs. TEMPERATURE

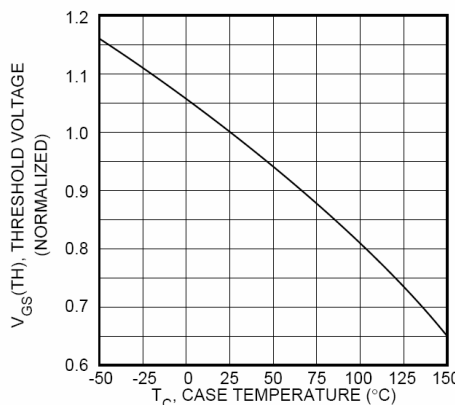


FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE

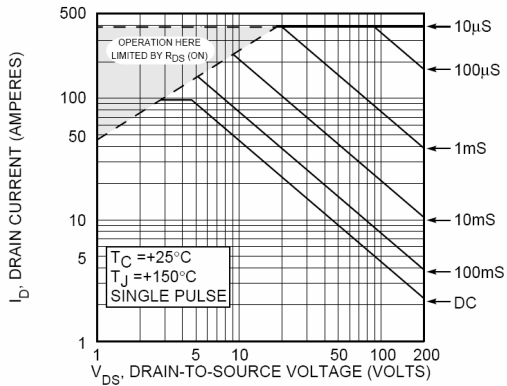


FIGURE 10, MAXIMUM SAFE OPERATING AREA

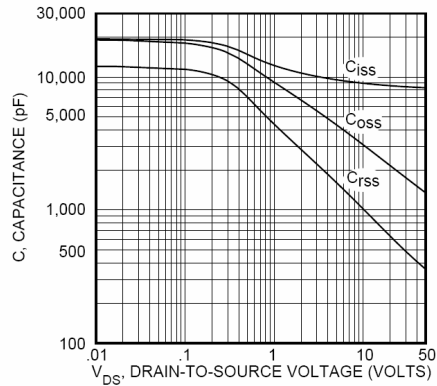


FIGURE 11, TYPICAL CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

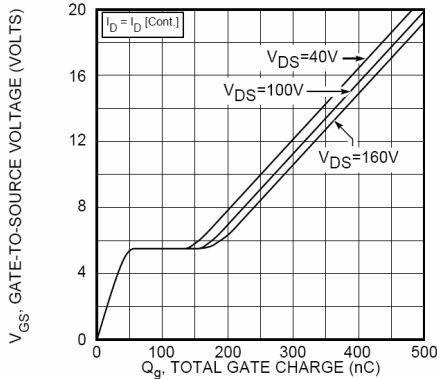


FIGURE 12, GATE CHARGES vs GATE-TO-SOURCE VOLTAGE

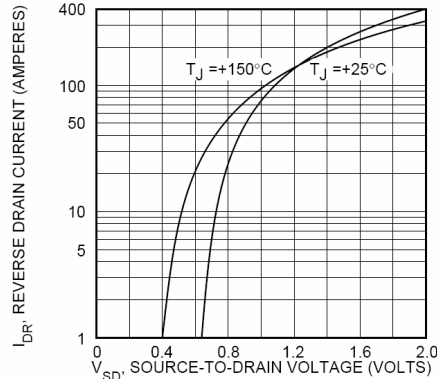


FIGURE 13, TYPICAL SOURCE-DRAIN DIODE FORWARD VOLTAGE

**Typical Diode Performance Curve**

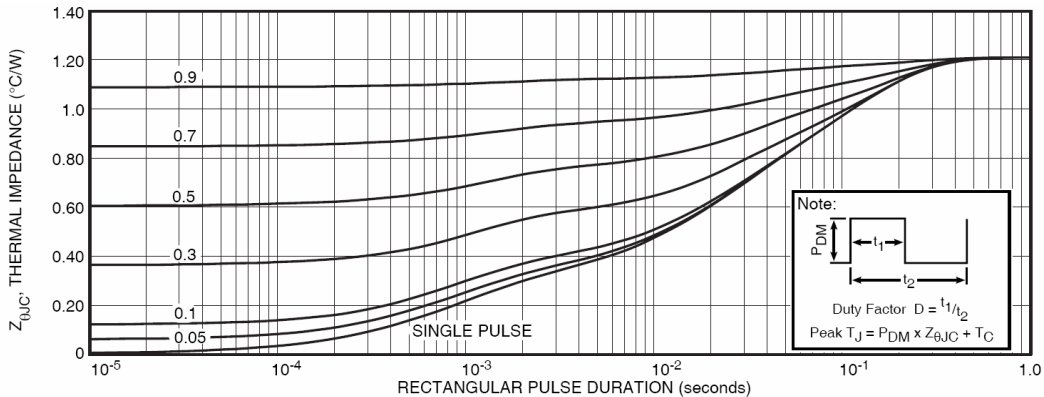


FIGURE 1a. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

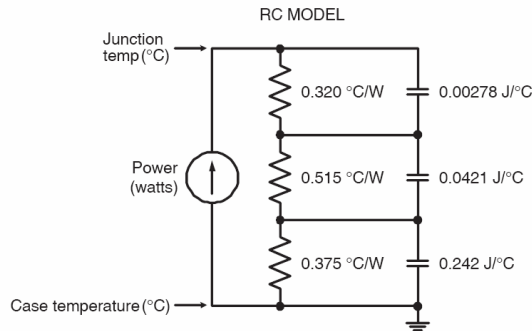


FIGURE 1b, TRANSIENT THERMAL IMPEDANCE MODEL

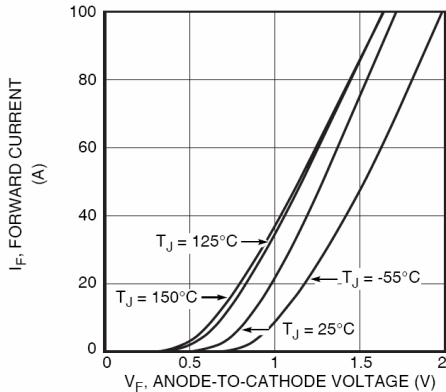


Figure 2. Forward Current vs. Forward Voltage

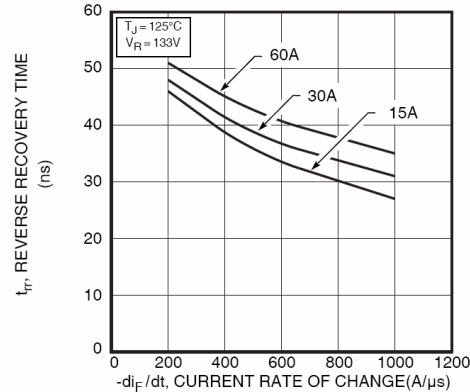


Figure 3. Reverse Recovery Time vs. Current Rate of Change

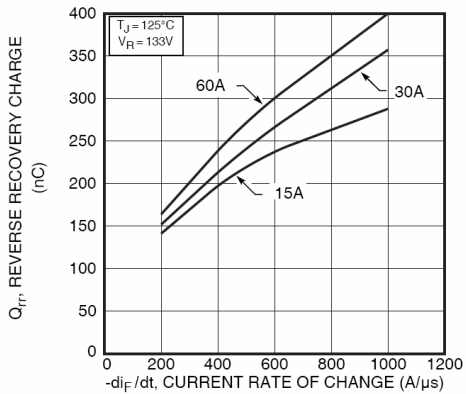


Figure 4. Reverse Recovery Charge vs. Current Rate of Change

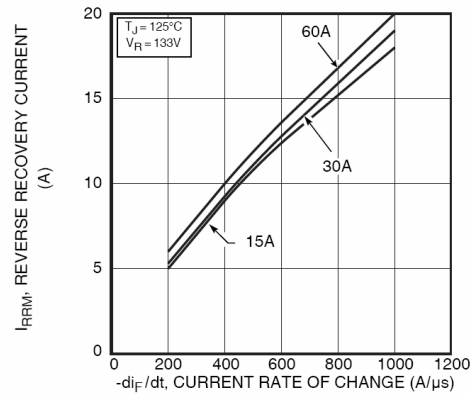


Figure 5. Reverse Recovery Current vs. Current Rate of Change

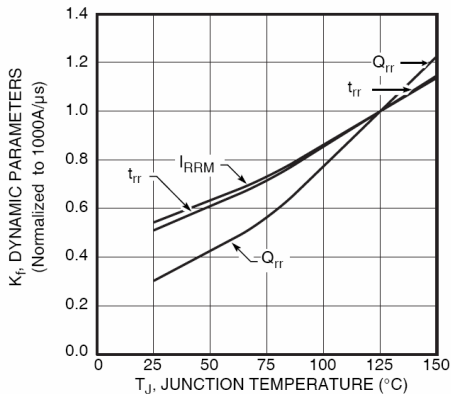


Figure 6. Dynamic Parameters vs. Junction Temperature

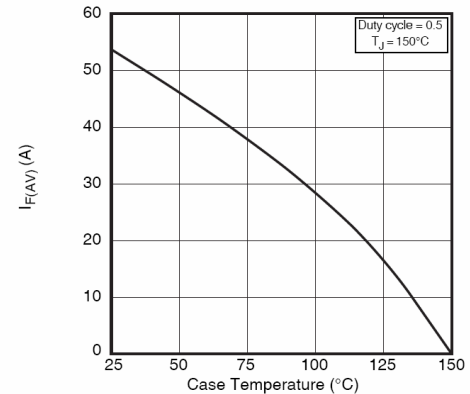


Figure 7. Maximum Average Forward Current vs. Case Temperature

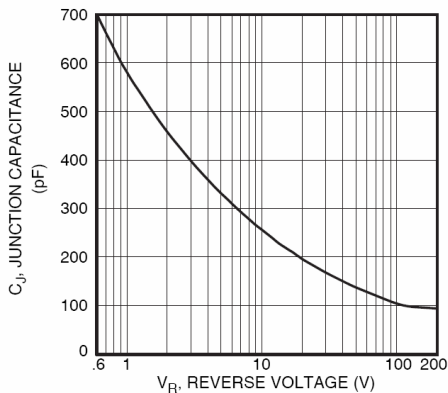


Figure 8. Junction Capacitance vs. Reverse Voltage

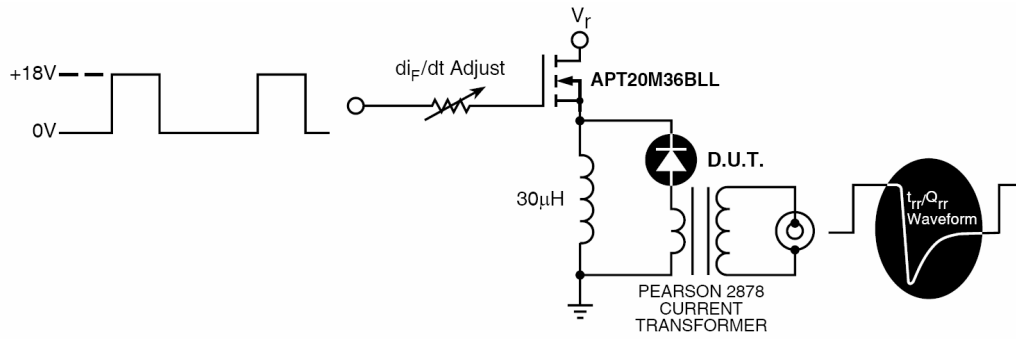


Figure 9. Diode Test Circuit

- 1  $I_F$  - Forward Conduction Current
- 2  $di_F/dt$  - Rate of Diode Current Change Through Zero Crossing.
- 3  $I_{RRM}$  - Maximum Reverse Recovery Current.
- 4  $t_{rr}$  - Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through  $I_{RRM}$  and  $0.25 \cdot I_{RRM}$  passes through zero.
- 5  $Q_{rr}$  - Area Under the Curve Defined by  $I_{RRM}$  and  $t_{rr}$ .

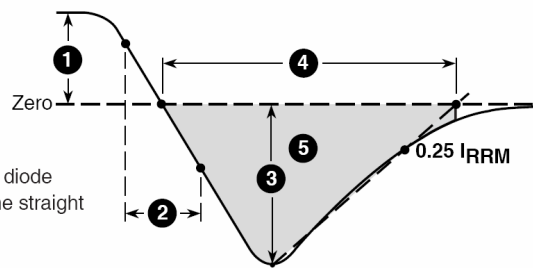
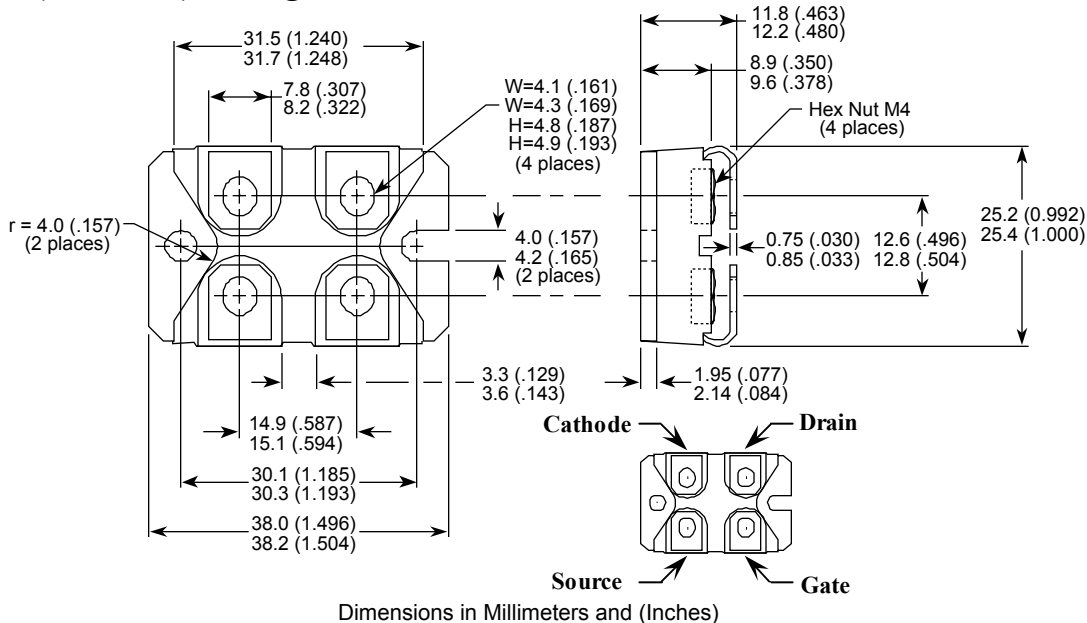


Figure 10, Diode Reverse Recovery Waveform and Definitions

**SOT-227 (ISOTOP®) Package Outline**



Dimensions in Millimeters and (Inches)

ISOTOP® is a Registered Trademark of SGS Thomson

APT reserves the right to change, without notice, the specifications and information contained herein

APT's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.